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August 24, 2007

Commissioner for Patents
PO Box 1450
Alexandria, VA 22313-1450

Re: **CERTIFICATE OF CORRECTION**

U. S. Letters Patent No. 7,153,784

Issued: December 26, 2006

For: **METHOD FOR MAKING A SEMICONDUCTOR
DEVICE HAVING A HIGH-K GATE
DIELECTRIC LAYER AND A METAL GATE
ELECTRODE**

Inventor: Brask, et al.


Our File No. 42390.P18609

Dear Sir:

Enclosed is the Certificate of Correction (two copies) for the above-referenced patent.
This request for correction is made under rule 322 of the Rules of Practice and 35 U.S.C.
Section 254.

Respectfully submitted,

BLAKELY, SOKOLOFF, TAYLOR & ZAFMAN LLP



Edwin H. Taylor
Reg. No. 25,129

EHT/sn
Enclosures

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,153,784
DATED : December 26, 2006
INVENTOR(S) : Brask et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In column 13, at line 5, delete "suicide" and insert --silicide--.

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PATENT NO. 7,153,784

Certificate of Correction (PTO Form 1050)-Amended